

ZXTP25020DZ 20V PNP high gain transistor in SOT89

Summary

 $BV_{CEO} > -20V$

 $BV_{ECO} > -4V$

 $I_{C(cont)} = 5A$

 $V_{CE(sat)} < -65 \text{mV} @ -1 \text{A}$

 $R_{CE(sat)} = 39m\Omega$

 $P_D = 2.4W$

Complementary part number ZXTN25020DZ



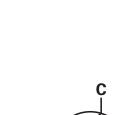
Packaged in the SOT89 outline this new low saturation 20V PNP transistor offers extremely low on state losses making it ideal for use in DC-DC circuits and various driving and power management functions

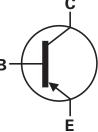
Features

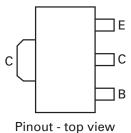
- · High peak current
- · Low saturation voltage
- · High gain
- SOT89 package

Applications

- · DC-DC converters
- · Load switch
- · Motor drive
- Disconnect switch
- · MOSFET and IGBT gate drive







Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTP25020DZTA	7	12	1000

Device marking

1L5

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-Base voltage	V _{CBO}	-25	V
Collector-Emitter voltage	V _{CEO}	-20	V
Emitter-Base voltage (reverse blocking)	V _{ECO}	-4	V
Emitter-Base voltage	V _{EBO}	-7	V
Continuous Collector current ^(c)	I _C	-5	Α
Base current	I _B	-1	Α
Peak pulse current	Ісм	-10	Α
Power dissipation at T _A =25°C ^(a)	P _D	1.1	W
Linear derating factor		8.8	mW/°C
Power dissipation at T _A =25°C ^(b)	P _D	1.8	W
Linear derating factor		14.4	mW/°C
Power dissipation at T _A =25°C ^(c)	P _D	2.4	W
Linear derating factor		19.2	mW/°C
Power dissipation at T _A =25°C ^(d)	P _D	4.46	W
Linear derating factor		35.7	mW/°C
Power dissipation at T _C =25°C ^(e)	P _D	15.7	W
Linear derating factor		126	mW/°C
Operating and storage temperature range	T _j , T _{stg}	-55 to 150	°C

Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient ^(a)	$R_{\Theta JA}$	117	°C/W
Junction to ambient ^(b)	$R_{\Theta JA}$	68	°C/W
Junction to ambient ^(c)	$R_{\Theta JA}$	51	°C/W
Junction to ambient ^(d)	$R_{\Theta JA}$	28	°C/W
Junction to case ^(e)	$R_{\Theta JC}$	7.95	°C/W

NOTES:

⁽a) For a device surface mounted on 15mm x 15mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

⁽b) Mounted on 25mm x 25mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

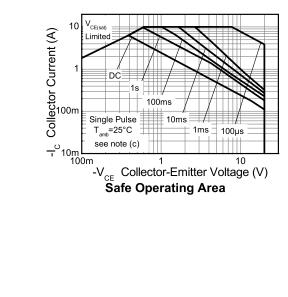
⁽c) Mounted on $50 \text{mm} \times 50 \text{mm} \times 0.6 \text{mm}$ FR4 PCB with high coverage of single sided 2oz copper, in still air conditions.

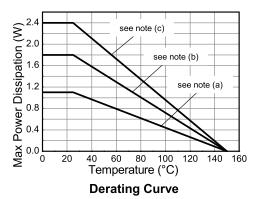
⁽d) As (c) above measured at t<5 seconds.

⁽e) Junction to case (collector tab). Typical.

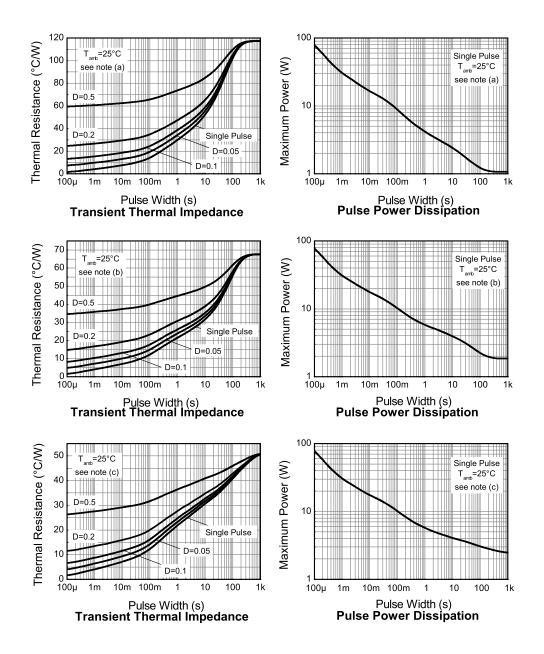
ZXTP25020DZ

Thermal characteristics





Thermal characteristics



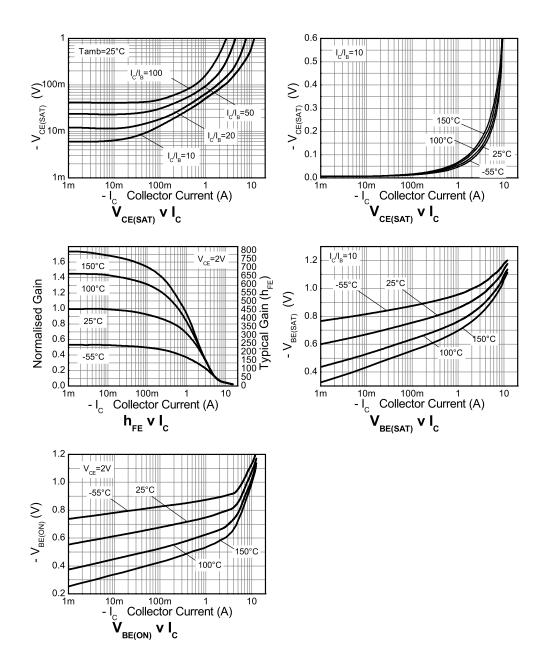
Electrical characteristics (at $T_{amb} = 25$ °C unless otherwise stated)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-Base breakdown voltage	BV _{CBO}	-25	-55		V	I _C = -100μA
Collector-Emitter breakdown voltage	BV _{CEO}	-20	-45		V	I _C = -10mA ^(*)
Emitter-Collector breakdown voltage (reverse blocking)	BV _{ECX}	-4	-8.5		V	I_E = -100μA, R_{BC} < 1kΩ or 0.25V > V_{BC} > -0.25V
Emitter-Collector breakdown voltage (reverse blocking)	BV _{ECO}	-4	-8.5		V	$I_E = -100 \mu A$
Emitter-Base breakdown voltage	BV _{EBO}	-7	-8.3		V	I _E = -5.6V
Collector-Base cut-off	I _{CBO}		<1	-50	nA	V _{CB} = -25V
current				-0.5	μΑ	$V_{CB} = -25V, T_{amb} = 100^{\circ}C$
Emitter cut-off current	I _{EBO}		<1	-50	nA	V _{EB} = -5.6V
Collector-Emitter	V _{CE(sat)}		-50	-65	mV	$I_C = -1A$, $I_B = -100 \text{mA}^{(*)}$
saturation voltage			-150	-215	mV	$I_C = -1A$, $I_B = -10mA^{(*)}$
			-185	-245	mV	$I_C = -2A$, $I_B = -40mA^{(*)}$
			-195	-265	mV	$I_C = -5A$, $I_B = -500 \text{mA}^{(*)}$
Base-Emitter saturation voltage	V _{BE(sat)}		-1010	-1100	mV	$I_C = -5A$, $I_B = -500 \text{mA}^{(*)}$
Base-Emitter turn-on voltage	V _{BE(on)}		-870	-1000	mV	$I_C = -5A$, $V_{CE} = -2V^{(*)}$
Static forward current	h _{FE}	300	450	900		$I_C = -10 \text{mA}, V_{CE} = -2V^{(*)}$
transfer ratio		200	310			$I_C = -1A$, $V_{CE} = -2V^{(*)}$
		45	85			$I_C = -5A$, $V_{CE} = -2V^{(*)}$
			20			$I_C = -10A$, $V_{CE} = -2V^{(*)}$
Transition frequency	f _T		290		MHz	$I_C = -50 \text{mA}, V_{CE} = -10 \text{V}$ f = 100MHz
Input capacitance	C _{ibo}		157	400	pF	V _{EB} = -0.5V, f = 1MHz ^(*)
Output capacitance	C _{obo}		21	30	pF	$V_{CB} = -10V, f = 1MHz^{(*)}$
Delay time	t _d		14.2		ns	
Rise time	t _r		16.3		ns	$V_{CC} = -10V, I_{C} = -1A,$
Storage time	t _s		186		ns	$I_{B1} = -I_{B2} = -50 \text{mA}$
Fall time	t _f		32.7		ns]

NOTES:

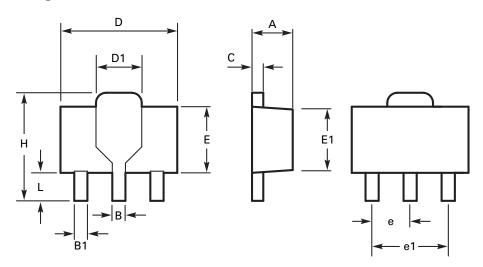
(*) Measured under pulsed conditions. Pulse width \leq 300µs; duty cycle \leq 2%.

Typical characteristics



ZXTP25020DZ

Package outline - SOT89



DIM	Millin	neters	Inc	hes	DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
Α	1.40	1.60	0.550	0.630	Е	2.29	2.60	0.090	0.102
В	0.44	0.56	0.017	0.022	E1	2.13	2.29	0.084	0.090
B1	0.36	0.48	0.014	0.019	е	1.50	BSC	0.059	BSC
С	0.35	0.44	0.014	0.017	e1	3.00	BSC	0.118	BSC
D	4.40	4.60	0.173	0.181	Н	3.94	4.25	0.155	0.167
D1	1.52	1.83	0.064	0.072	L	0.89	1.20	0.035	0.047

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

ZXTP25020DZ

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8

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